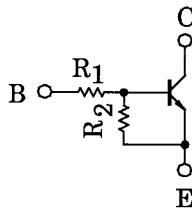


TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

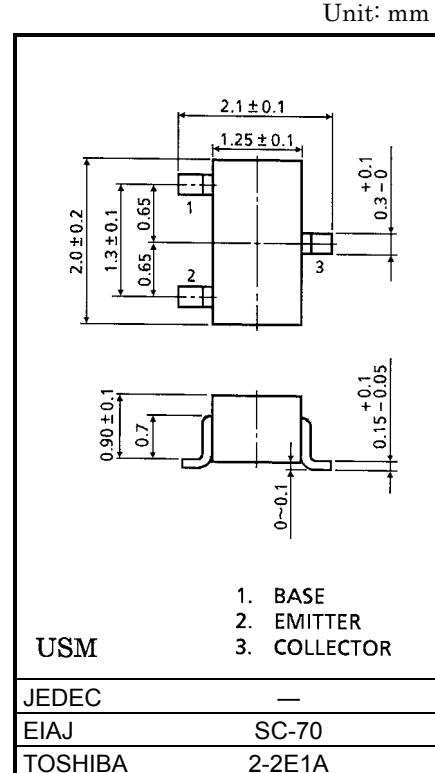
**RN1314,RN1315,RN1316  
RN1317,RN1318**

Switching, Inverter Circuit, Interface Circuit  
And Driver Circuit Applications

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Complementary to RN2314~RN2318

**Equivalent Circuit and Bias Resistor Values**

Type No.	R1 (kΩ)	R2 (kΩ)
RN1314	1	10
RN1315	2.2	10
RN1316	4.7	10
RN1317	10	4.7
RN1318	47	10

**Maximum Ratings (Ta = 25°C)**

Characteristic		Symbol	Rating	Unit
Collector-base voltage	RN1314~1318	V <sub>CBO</sub>	50	V
Collector-emitter voltage		V <sub>CEO</sub>	50	V
Emitter-base voltage	RN1314	V <sub>EBO</sub>	5	V
			6	
			7	
			15	
			25	
Collector current	RN1314~1318	I <sub>C</sub>	100	mA
Collector power dissipation		P <sub>C</sub>	100	mW
Junction temperature		T <sub>j</sub>	150	°C
Storage temperature range		T <sub>stg</sub>	-55~150	°C

## Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Circuit	Test Condition		Min	Typ.	Max	Unit
Collector cut-off current	RN1314~1318	ICBO	—	V <sub>CB</sub> = 50V, I <sub>E</sub> = 0		—	—	100	nA
	RN1314~1318	ICEO		V <sub>CE</sub> = 50V, I <sub>B</sub> = 0		—	—	500	nA
Emitter cut-off current	RN1314	IEBO	—	V <sub>EB</sub> = 5V, I <sub>C</sub> = 0		0.35	—	0.65	mA
	RN1315			V <sub>EB</sub> = 6V, I <sub>C</sub> = 0		0.37	—	0.71	
	RN1316			V <sub>EB</sub> = 7V, I <sub>C</sub> = 0		0.36	—	0.68	
	RN1317			V <sub>EB</sub> = 15V, I <sub>C</sub> = 0		0.78	—	1.46	
	RN1318			V <sub>EB</sub> = 25V, I <sub>C</sub> = 0		0.33	—	0.63	
DC current gain	RN1314~16,18	$\text{h}_{\text{FE}}$	—	V <sub>CE</sub> = 5V, I <sub>C</sub> = 10mA		50	—	—	
	RN1317					30	—	—	
Collector-emitter saturation voltage	RN1314~1318	V <sub>CE</sub> (sat)	—	I <sub>C</sub> = 5mA, I <sub>B</sub> = 0.25mA		—	0.1	0.3	V
Input voltage (ON)	RN1314	V <sub>I</sub> (ON)	—	V <sub>CE</sub> = 0.2V, I <sub>C</sub> = 5mA		0.6	—	2.0	V
	RN1315					0.7	—	2.5	
	RN1316					0.8	—	2.5	
	RN1317					1.5	—	3.5	
	RN1318					2.5	—	10.0	
Input voltage (OFF)	RN1314	V <sub>I</sub> (OFF)	—	V <sub>CE</sub> = 5V, I <sub>C</sub> = 0.1mA		0.3	—	0.9	V
	RN1315					0.3	—	1.0	
	RN1316					0.3	—	1.1	
	RN1317					0.3	—	2.3	
	RN1318					0.5	—	5.7	
Transition frequency	RN1314~1318	f <sub>T</sub>	—	V <sub>CE</sub> = 10V, I <sub>C</sub> = 5mA		—	250	—	MHz
Collector Output capacitance	RN1314~1318	C <sub>ob</sub>	—	V <sub>CB</sub> = 10V, I <sub>E</sub> = 0, f = 1MHz		—	3.0	6.0	pF
Input resistor	RN1314	R <sub>1</sub>	—	—		0.7	1.0	1.3	kΩ
	RN1315					1.54	2.2	2.86	
	RN1316					3.29	4.7	6.11	
	RN1317					7.0	10.0	13.0	
	RN1318					32.9	47.0	61.1	
Resistor ratio	RN1314	R <sub>1</sub> /R <sub>2</sub>	—	—		—	0.1	—	
	RN1315					—	0.22	—	
	RN1316					—	0.47	—	
	RN1317					—	2.13	—	
	RN1318					—	4.7	—	

